

isc Silicon PNP Darlington Power Transistor

BD684

DESCRIPTION

- Collector–Emitter Breakdown Voltage—
- $: V_{(BR)CEO} = -120V$
- DC Current Gain-
 - : $h_{FE} = 750(Min)$ @ $I_{C} = -1.5 A$
- Complement to Type BD683
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

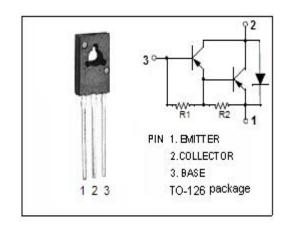
· Designed for audio and video output applications.

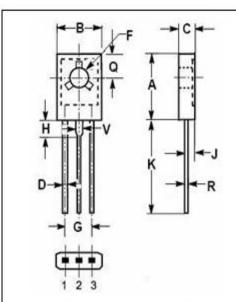
ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

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PARAMETER	VALUE	UNIT					
Collector-Base Voltage	-120	V					
Collector-Emitter Voltage	-120	V					
Emitter-Base Voltage	-5	V					
Collector Current-Continuous	-4	Α					
Collector Current-Peak	-6	Α					
Base Current	-0.1	Α					
Collector Power Dissipation T _C =25°C	40	W					
Junction Temperature	150	$^{\circ}\!\mathbb{C}$					
Storage Temperature Range	-65~150	$^{\circ}$					
	PARAMETER Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Collector Current-Continuous Collector Current-Peak Base Current Collector Power Dissipation Tc=25°C Junction Temperature	PARAMETER Collector-Base Voltage Collector-Emitter Voltage -120 Emitter-Base Voltage -5 Collector Current-Continuous -4 Collector Current-Peak -6 Base Current Collector Power Dissipation Tc=25℃ Junction Temperature 150					

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
Rth j-c	Thermal Resistance, Junction to Case	3.12	°C/W





	m	m
DIM	MIN	MAX
Α	10.70	10.95
В	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
Н	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
٧	1.17	1.37



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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA; I _B = 0	-120		V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -1.5A; I _B = -6mA		-2.5	V
$V_{\text{BE(on)}}$	Base-Emitter On Voltage	I _C = -1.5A; V _{CE} = -3V		-2.5	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -60V; I _B = 0		-0.5	mA
Ісво	Collector Cutoff Current	V _{CB} = -120V; I _E = 0 V _{CB} = -120V; I _E = 0;T _C = 100°C		-0.2 -2.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0		-5.0	mA
h _{FE}	DC Current Gain	I _C = -1.5 A; V _{CE} = -3V	750		

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